

✳️ Assignments :- B.1.b (Using 90nm Foundry)

(I) B.L.b :-

- a) 2 i/p NAND
- b) 2 i/p NOR
- c) 2 i/p AND
- d) 2 i/p OR

✳️ 2 i/p NAND, 2 i/p NOR Gates:-

2 i/p NAND



2 i/p NOR



Symbols:

Expression:

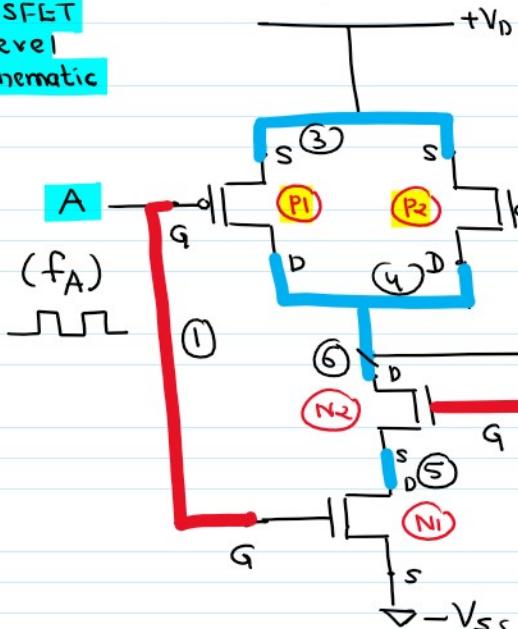
$$Y_{nand} = \overline{A \cdot B}$$

(P₁//P₂), (N₁-N₂)

$$Y_{nor} = \overline{A + B}$$

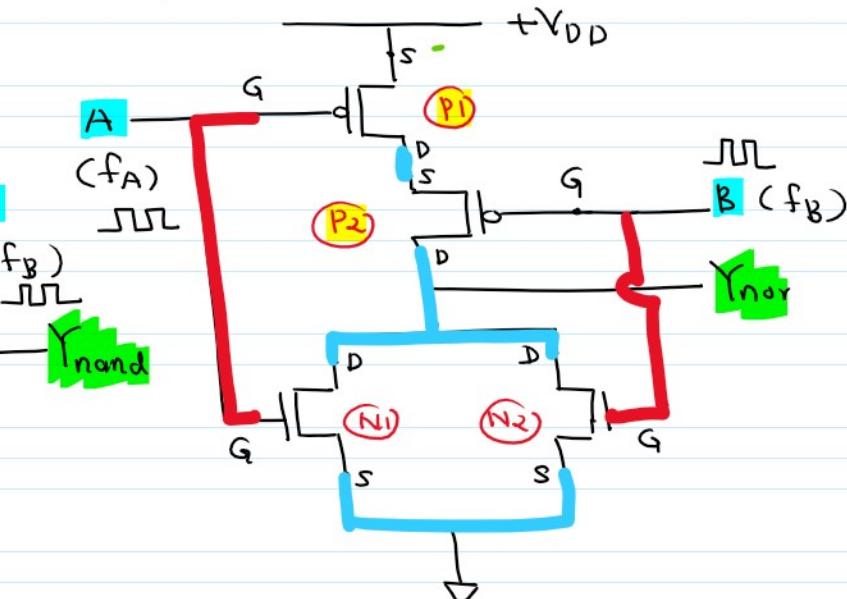
(P₁-P₂), (N₁//N₂)

MOSFET Level Schematic



$$f_A = \frac{1}{2} \cdot f_B$$

T_A T_B



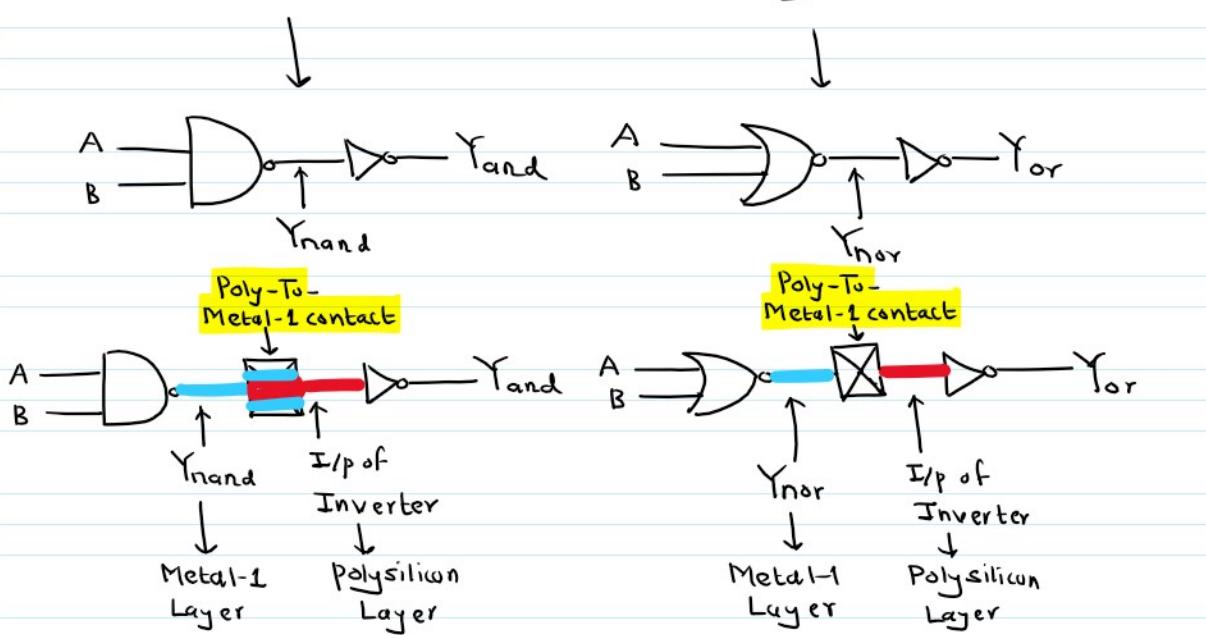
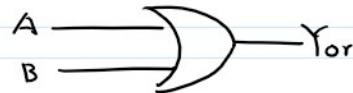
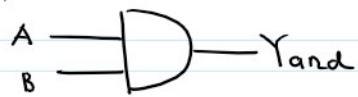
$$f_A = \frac{1}{2} f_B$$

T_A	T_B	Y_{NAND}
A	B	Y_{NAND}
0	0	1
0	1	1
1	0	1
1	1	0

A	B	Y_{NOR}
A	B	Y_{NOR}
0	0	1
0	1	0
1	0	0
1	1	0

(*) 2 i/p AND, 2 i/p OR gate:-

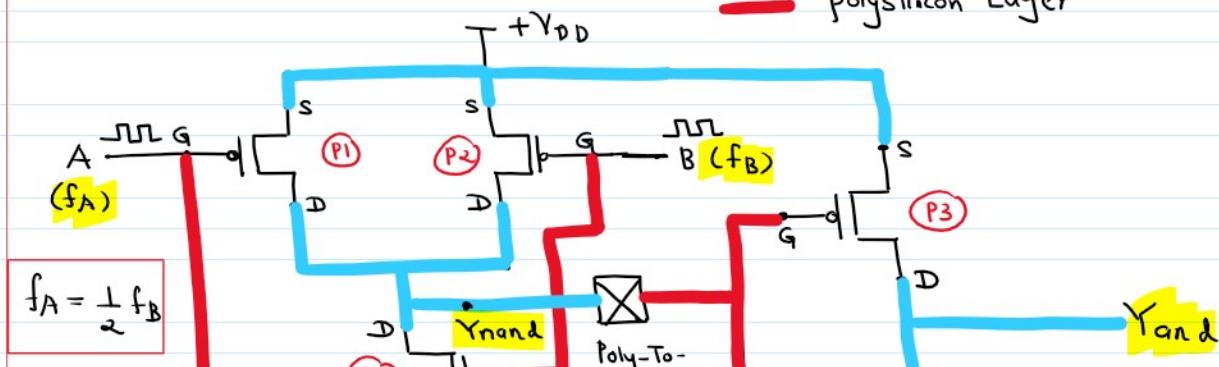
Symbols:-

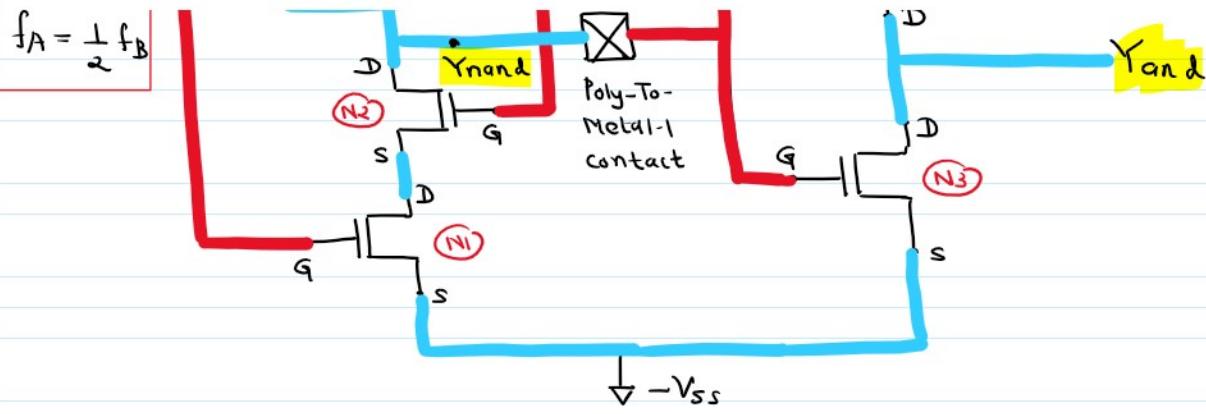


(*) MOSFET-Level Schematics for 2 i/p AND, 2 i/p OR Gate :-

(*) 2 i/p AND Gate :-

— Meta-1 Layer
— Polysilicon Layer





⊗ 2yp OR Gate :-

